

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 100V, I_D = 65A$
 $R_{DS(ON)} = 7.0m\Omega$, typical @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(ON)}$ product (FOM)
- Very low on-resistance $R_{DS(ON)}$
- 150 °C operating temperature
- Pb-free lead plating

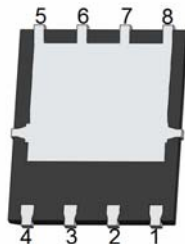
100% UIS TESTED!

100% ΔVds TESTED!

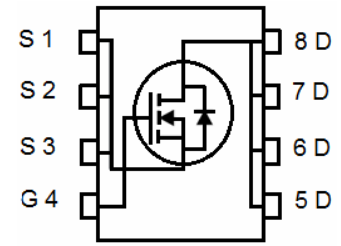
DFN 5X6



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P090N10GU	NCEP090N10GU	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ^(Note 1)	I_D	65	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	47	A
Pulsed Drain Current	I_{DM}	260	A
Maximum Power Dissipation	P_D	85	W
Derating factor		0.68	W/ $^\circ C$
Single pulse avalanche energy ^(Note 4)	E_{AS}	288	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.47	$^\circ C/W$
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =32.5A	-	7.0	9.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =32.5A		50	-	S
Dynamic Characteristics (Note 3)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	2160	-	pF
Output Capacitance	C _{oss}		-	289	-	pF
Reverse Transfer Capacitance	C _{rss}		-	20	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =32.5A V _{GS} =10V, R _G =1.6Ω	-	12	-	nS
Turn-on Rise Time	t _r		-	9	-	nS
Turn-Off Delay Time	t _{d(off)}		-	29	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =32.5A, V _{GS} =10V	-	42	-	nC
Gate-Source Charge	Q _{gs}		-	14	-	nC
Gate-Drain Charge	Q _{gd}		-	12.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V _{SD}	V _{GS} =0V, I _S =32.5A	-	-	1.2	V
Diode Forward Current	I _S		-	-	65	A
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 32.5A di/dt = 100A/μs (Note 3)	-	55	-	nS
Reverse Recovery Charge	Q _{rr}		-	98	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
3. Guaranteed by design, not subject to production
4. EAS condition : T_J=25 °C, V_{DD}=50V, V_G=10V, L=0.25mH, R_G=25Ω

Typical Electrical and Thermal Characteristics

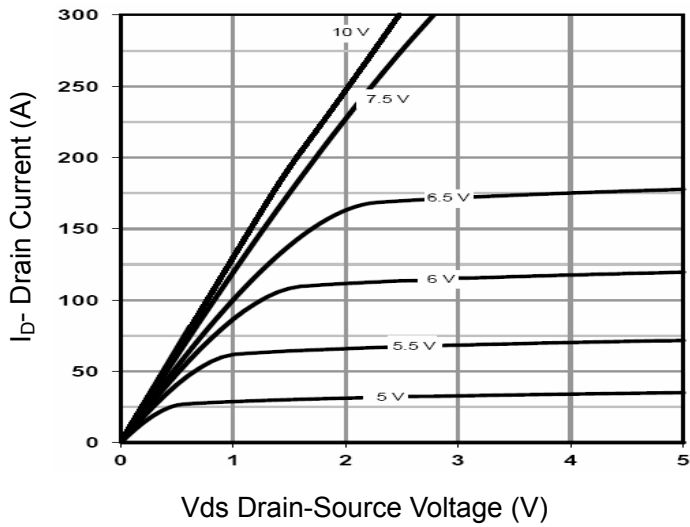


Figure 1 Output Characteristics

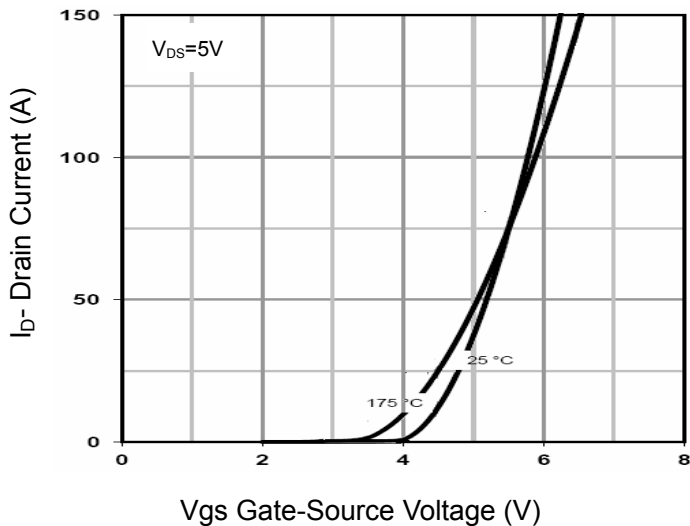


Figure 2 Transfer Characteristics

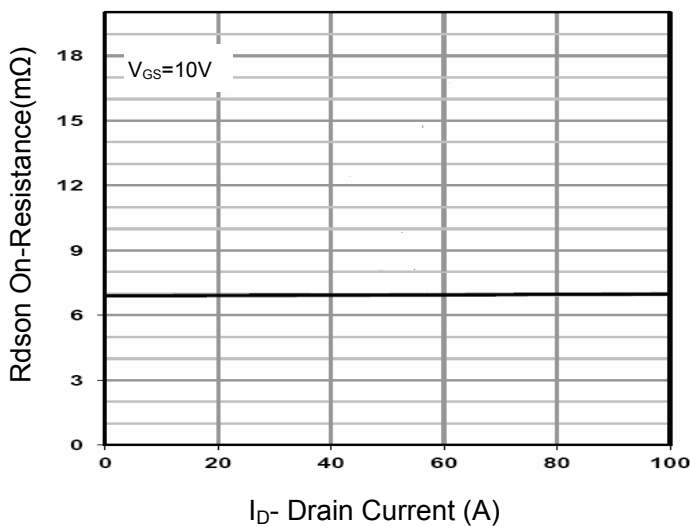


Figure 3 $R_{DS(on)}$ - Drain Current

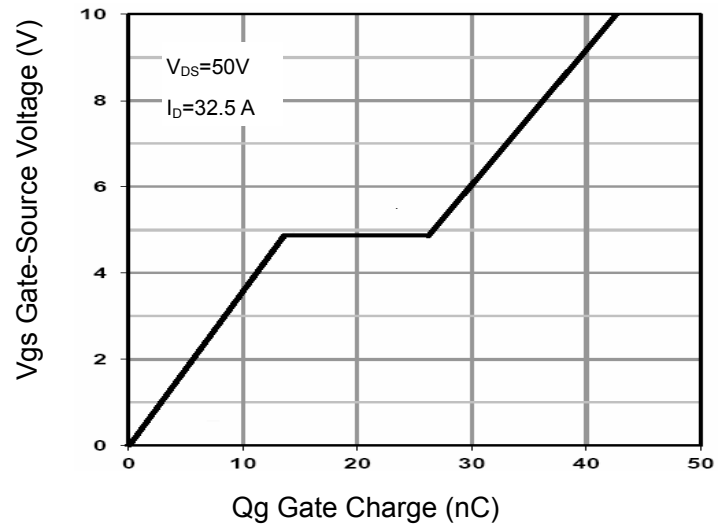


Figure 4 Gate Charge

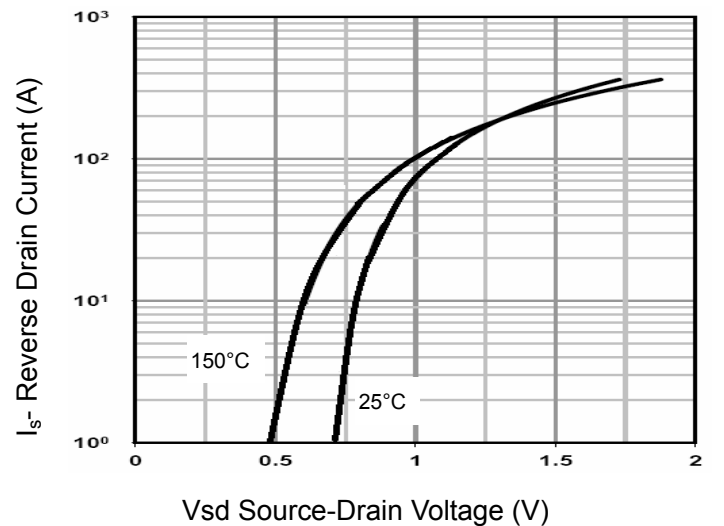


Figure 5 Source- Drain Diode Forward

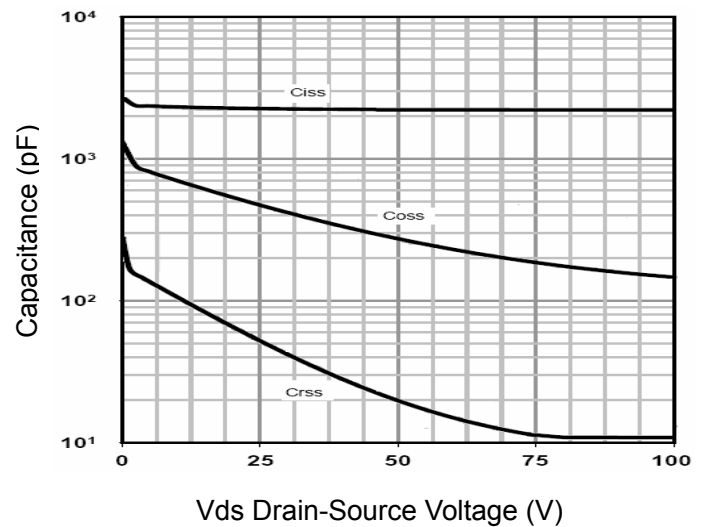
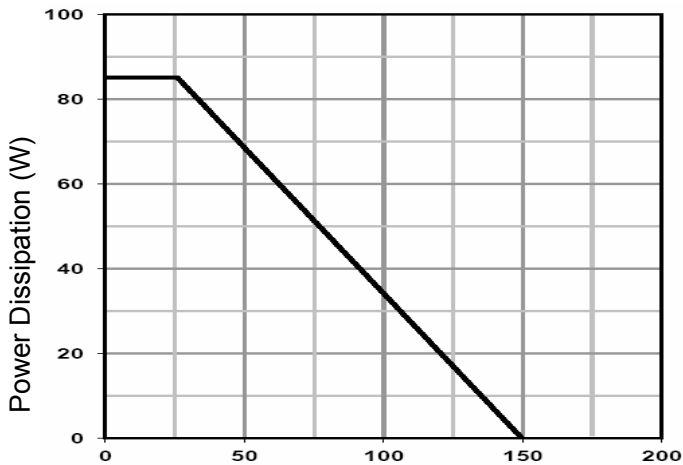
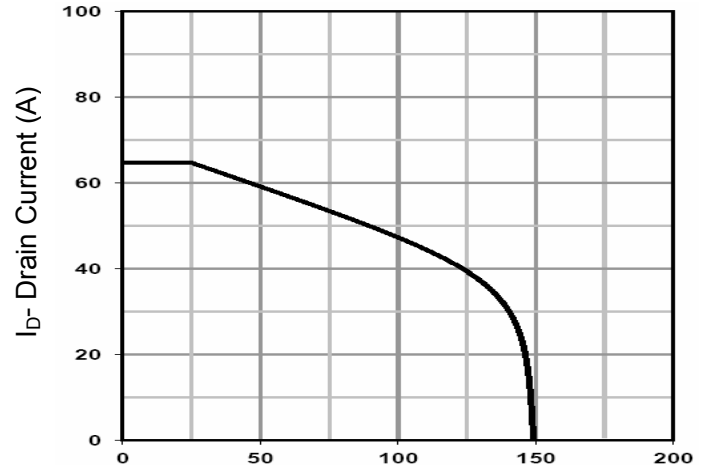


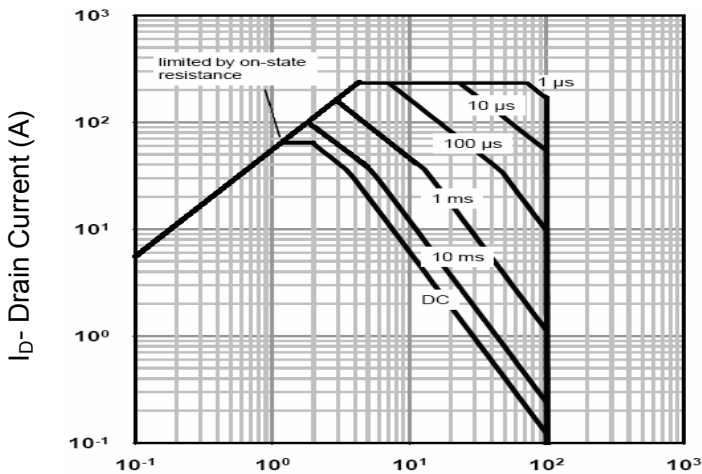
Figure 6 Capacitance vs V_{DS}



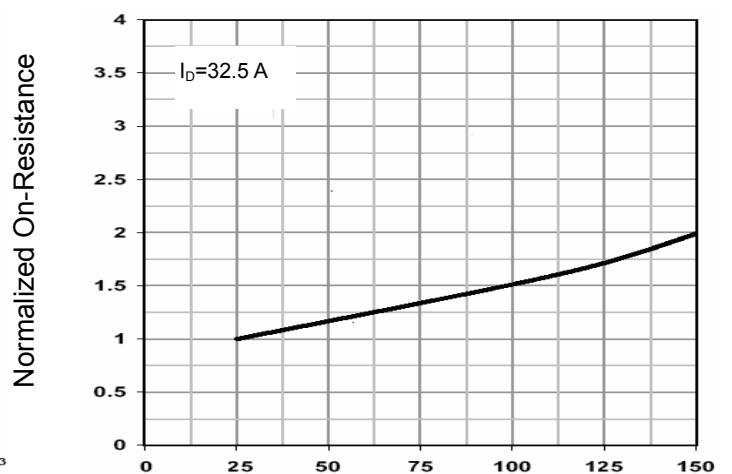
T_J-Junction Temperature(°C)
Figure 7 Power De-rating



T_J-Junction Temperature (°C)
Figure 9 Current De-rating



V_{ds} Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J-Junction Temperature(°C)
Figure 10 Rdson-Junction Temperature

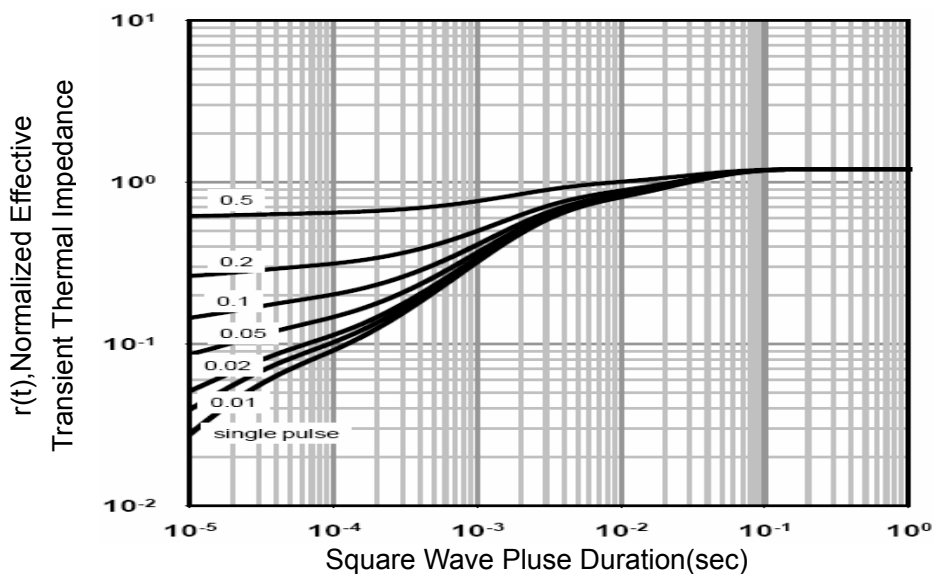
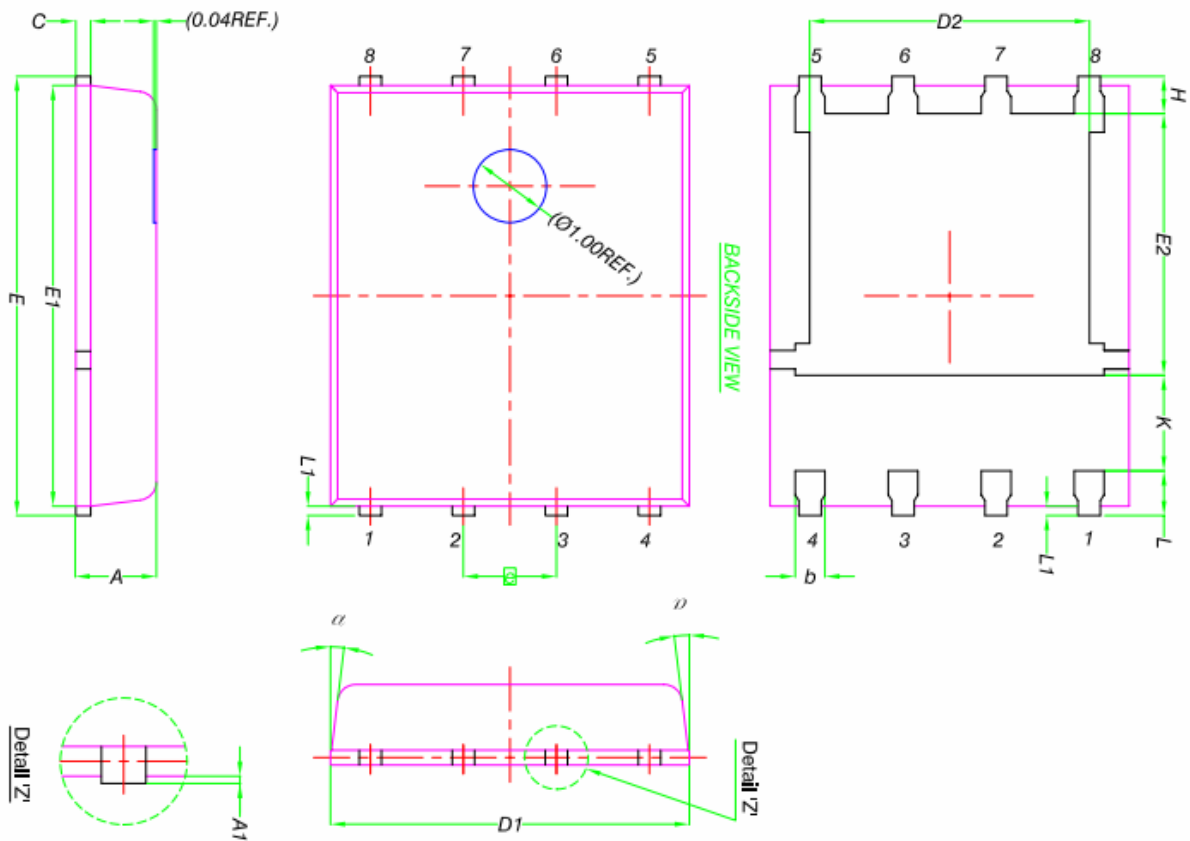
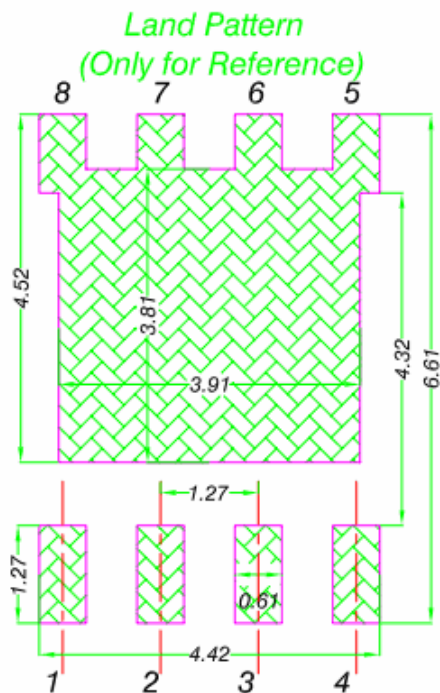


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°



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